

Schottky junction

$$x_d(v) = \sqrt{\frac{2\epsilon(\phi_{bi} - v)}{qN_D}}$$

Energy barrier decreases under forward bias.

$\therefore$ # electrons increases exponentially with v .

$\therefore$ thinking in terms of electron population explains the rectifying behavior

* $v=0$ drift = diffusion

* electron thermalize in metal

* Boltzmann: reaching the interface

$\Rightarrow$ for high $\mu \Rightarrow$ electrons reach the interface quite easily.

emission $\Rightarrow$ focus at the tip of the energy band: thermionic emission

Thermionic - emission theory:

$$J_t \approx J_e(0^+) = J_{e,sm}(0^+) - J_{e,rs}(0^+)$$

$$J_{e,sm}(0^+) \approx -q \cdot n(0^+) \cdot v_e(0^+)$$

$$n(0^+) = \frac{n(lce)}{2} \cdot \exp \frac{q[\phi(0^+) - \phi(lce)]}{kT} \quad [1]$$

at $x=lce$

only half of the electrons have the v_e pointing to the interface

$$\begin{cases} n(lce) \approx N_D \exp \frac{+q\phi(lce)}{kT} \\ \phi(0^+) = -(\phi_{bi} - v) \end{cases}$$

Using [1] $\Rightarrow n(0^+) = \frac{N_D}{2} \exp \left(\frac{q\phi(lce)}{kT} \right) \cdot \exp \left[-\frac{q(\phi_{bi} - v)}{kT} \right] \cdot \exp \left(-\frac{q\phi(lce)}{kT} \right)$

$$\therefore n(0^+) = \frac{N_D}{2} \exp \left(-\frac{q(\phi_{bi} - v)}{kT} \right) = \frac{N_C}{2} \exp \left(-\frac{q(\phi_{bn} - v)}{kT} \right)$$

only half of the $n(0^+)$ in T.E

$$* N_D \cdot \exp \left(-\frac{\phi_{bi}}{kT} \right) = N_C \cdot \exp \left(-\frac{q\phi_{bn}}{kT} \right)$$

in TE

$$n(0^+) = N_D \exp \frac{-q(\phi_{bi} - v)}{kT}$$

but this is not valid!

Some electron ~~concentration~~ concentration ~~is~~ is different than in equilibrium.

$\hookrightarrow$ not enough collisions with the lattice $\Rightarrow$ not in equilibrium

Second : v_{th}

taking into account statistics :

$$v_e(0^+) = -\frac{v_{th}}{2} = -\sqrt{\frac{ZkT}{\pi m_{ec}}}$$

$$\therefore J_{e,sm} = q \cdot N_c \cdot \underbrace{\sqrt{\frac{kT}{2\pi m_{ec}}}}_{A^* \cdot T^2} \exp \frac{-q\phi_{bn}}{kT} \cdot \exp \left(\frac{qV}{kT} \right)$$

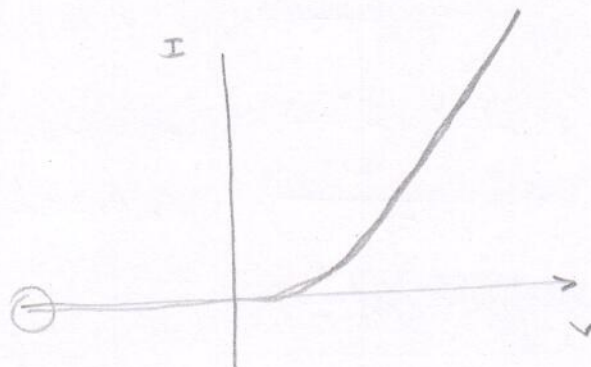
$$A^* = \frac{4\pi q k^2 m_o}{h^3} \sqrt{\frac{(m_{di}/m_o)^3}{(m_{ec}/m_o)}} \quad \text{Richardson's constant}$$

and

$$J_{e,ns} = ? \quad \Rightarrow \quad J_t = 0 \quad \text{when} \quad V=0$$

$$\therefore J_{e,ns} = A^* T^2 \exp \left(-\frac{q\phi_{bn}}{kT} \right)$$

$$\boxed{J_t = A^* T^2 \exp \left(-\frac{q\phi_{bn}}{kT} \right) \left(\exp \frac{qV}{kT} - 1 \right)}$$



$$I_s = A_j \cdot A^* T^2 \exp \left(-\frac{q\phi_{bn}}{kT} \right)$$

Ohmic contacts

$$x_d = \sqrt{\frac{2 \cdot \epsilon (\phi_{bi} - V)}{q N_D}}$$

$$1) N_D \uparrow \Rightarrow x_d \downarrow$$

$$2) q\phi_{bn} = q\phi_{bi} + \underbrace{q\phi_{bn}}_{(E_c - E_f)} \Rightarrow \downarrow \phi_{bn} \Rightarrow \downarrow \phi_{bi} \Rightarrow x_d \downarrow$$

$$J \approx A^* T^2 \underbrace{\exp\left(-\frac{q\phi_{bn}}{kT}\right)}_{\approx 1} \cdot \underbrace{\exp\left(\frac{qV}{kT}\right)}_{\substack{\uparrow \\ \text{small } V}} \approx \frac{V}{\rho_c}$$